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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/612,793	07/02/2003	Arup Bhattacharyya	1303.111US1	5437	
7	590 08/27/2004	EXAMINER			
	Lundberg, Woessner	ERDEM	ERDEM, FAZLI		
Attn: Marvin L	Beekman				
P.O. Box 2938		ART UNIT	PAPER NUMBER		
Minneapolis, I	MN 55402	2826			

DATE MAILED: 08/27/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

·		Application	on No.	Applicant(s)			
Office Action Summary		10/612,79	93	BHATTACHARYYA, ARUP			
		Examine)	Art Unit)		
		Fazli Erde	em	2826	gr		
Period fe	The MAILING DATE of this communication a or Reply	appears on the	cover sheet with the d	correspondence ad	idress		
THE - Exte after - If the - If NC - Failt Any	ORTENED STATUTORY PERIOD FOR REF MAILING DATE OF THIS COMMUNICATION nsions of time may be available under the provisions of 37 CFR SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a to period for reply is specified above, the maximum statutory perior to reply within the set or extended period for reply will, by stareply received by the Office later than three months after the may ed patent term adjustment. See 37 CFR 1.704(b).	N. 1.136(a). In no ever reply within the stat iod will apply and w tute, cause the app	ent, however, may a reply be tir utory minimum of thirty (30) day ill expire SIX (6) MONTHS from lication to become ABANDONE	mely filed ys will be considered time n the mailing date of this c ED (35 U.S.C. § 133).			
Status							
1)[\]	Responsive to communication(s) filed on 22	2 March 2004.					
2a)[☐	☐ This action is FINAL . 2b)⊠ This action is non-final.						
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposit	ion of Claims						
5)⊠ 6)⊠ 7)□							
Applicat	ion Papers						
9)[The specification is objected to by the Exami	iner.					
10)	10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.						
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11)□	Replacement drawing sheet(s) including the corr The oath or declaration is objected to by the	•	-, <i>,</i>	•	` '		
Priority (under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
Attachmen	t(s)						
1) Notic	e of References Cited (PTO-892)		4) Interview Summary				
3) 🛛 Infor	e of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/0 r No(s)/Mail Date <u>03/01/2004</u> .	08)	Paper No(s)/Mail D 5) Notice of Informal F 6) Other:		O-152)		

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DETAILED ACTION

Allowable Subject Matter

1. Claims 6-53 and 72-79 allowed.

2. The following is a statement of reasons for the indication of allowable subject matter:

Regarding Claim 6, prior art failed to establish a memory cell having first diffusion region connected to bit line, a second diffusion region which store the memory state of the memory cell, a negative differential resistance diode with an intrinsic region between the anode and cathode to assist with stabilizing the memory stat of the memory cell, connected between the second diffusion region and the reference potential line.

Regarding Claims 7-53, prior art failed to establish a p-channel or n-channel access transistor with a first and second p or n-type diffusion region where the second p or n-type diffusion region store the memory state of the memory cell and a negative differential resistance n/i/p or p/i/n diode having n or p-type anode and cathode with an intrinsic region between the anode and cathode to assist with stabilizing the memory state of the memory cell.

Regarding Claims 72-79, prior art failed to establish a memory device with memory array, word lines, bit lines with access transistor with first and second diffusion regions, a negative differential resistance diode with an intrinsic region between the anode and the cathode where the memory cell is used to store charge in the second diffusion region.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

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(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

3. Claims 1-5 and 54-71 rejected under 35 U.S.C. 103(a) as being unpatentable over Han (6,611,452) in view of Babcock et al. (6,660,616).

Regarding Claims 1-5 and 54-71, Han discloses reference cells fro TCCT based memory cells where a reference cell produces a voltage rise on a bit line that is proportional rise on a another bit line produced by a TCCT based memory cell in an "on" state. The reference cell includes an NDR device, a gate line device disposed adjacent to the NDR device, a first resistive element coupled between the NDR device and the bit line, and a second resistive element coupled between a sink and the bit line. Han fails to disclose the required intrinsic region requirement. However, Babcock et al. disclose a P-I-N transit time silicon-on-insulator device where in columns 3 and 5, the required intrinsic region configuration is disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required intrinsic region configuration in Han as taught by Babcock et al. in order to have a memory cell with higher performance.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (703) 305-3868. The examiner can normally be reached on M - F 8:00 - 5:00.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (703) 308-6601. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE May 30, 2004

MATHAN J FLYNN SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800